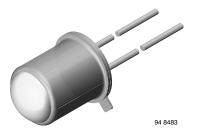
Vishay Semiconductors



Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAIAs



TSTA7100 is an infrared, 875 nm emitting diode in GaAlAs technology in a hermetically sealed TO-18 package with

FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): Ø 4.7
- Peak wavelength: $\lambda_p = 875 \text{ nm}$
- High reliability
- High radiant power
- · High radiant intensity
- Angle of half intensity: $\phi = \pm 5^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

• Radiation source near infrared range

PRODUCT SUMMARY COMPONENT Ie (mW/sr) φ (deg) λP (nm) tr (ns) TSTA7100 50 ±5 875 600

Note

lens.

DESCRIPTION

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | | | | |
|----------------------|-----------|------------------------------|--------------|--|--|--|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | | | | |
| TSTA7100 | Bulk | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18 | | | | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|-------------------------------------|--------------------------------|-------------------|---------------|------|--|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | | |
| Reverse voltage | | V _R | 5 | V | | |
| Forward current | | I _F | 100 | mA | | |
| Peak forward current | $t_p/T=0.5,t_p\leq 100\;\mu s$ | I _{FM} | 200 | mA | | |
| Surge forward current | $t_p \le 100 \ \mu s$ | I _{FSM} | 2.5 | А | | |
| Devuer disaination | | Pv | 180 | mW | | |
| Power dissipation — | $T_{case} \le 25 \ ^{\circ}C$ | Pv | 500 | mW | | |
| Junction temperature | | Tj | 100 | °C | | |
| Storage temperature range | | T _{stg} | - 55 to + 100 | °C | | |
| Thermal resistance junction/ambient | leads not soldered | R _{thJA} | 450 | K/W | | |
| Thermal resistance junction/case | leads not soldered | R _{thJC} | 150 | K/W | | |

Note

 T_{amb} = 25 °C, unless otherwise specified





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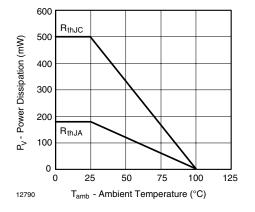


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

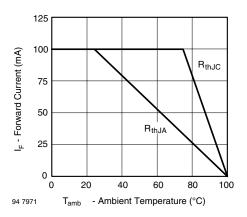


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | | |
|---------------------------------------|---|-------------------|------|-------|------|-------|--|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT | |
| Forward voltage | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$ | V _F | | 1.4 | 1.8 | V | |
| Breakdown voltage | I _R = 100 μA | V _(BR) | 5 | | | V | |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | Cj | | 20 | | pF | |
| Radiant intensity | I_F = 100 mA, $t_p \le$ 20 ms | l _e | 20 | 50 | 100 | mW/sr | |
| Radiant power | I_F = 100 mA, $t_p \le$ 20 ms | φe | | 10 | | mW | |
| Temperature coefficient of ϕ_{e} | I _F = 100 mA | TKφ _e | | - 0.7 | | %/K | |
| Angle of half intensity | | φ | | ± 5 | | deg | |
| Peak wavelength | I _F = 100 mA | λρ | | 875 | | nm | |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 80 | | nm | |
| Rise time | I _F = 100 mA | t _r | | 600 | | ns | |
| | $I_F = 1.5 \text{ A}, t_p/T = 0.01, t_p \le 10 \ \mu s$ | tr | | 300 | | ns | |
| Virtual source diameter | | d | | 1.5 | | mm | |

Note

 T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

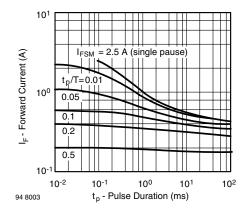


Fig. 3 - Pulse Forward Current vs. Pulse Duration

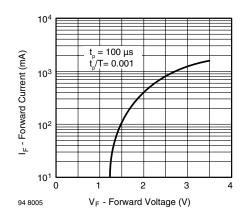


Fig. 4 - Forward Current vs. Forward Voltage

TSTA7100



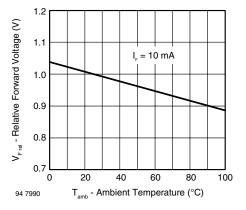


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

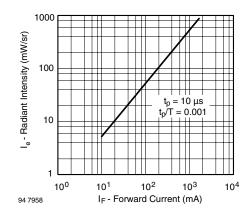


Fig. 6 - Radiant Intensity vs. Forward Current

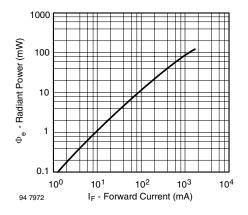


Fig. 7 - Radiant Power vs. Forward Current

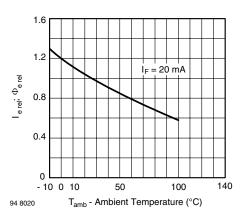


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

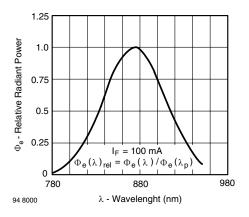


Fig. 9 - Relative Radiant Power vs. Wavelength

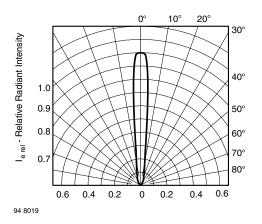
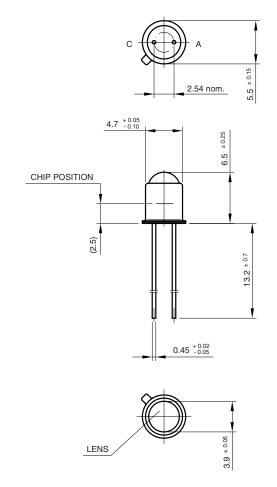


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.503-5002.01-4 Issue: 2; 24.08.98 96 12174



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